



# STGB19NC60HD - STGF19NC60HD STGP19NC60HD - STGW19NC60HD

19 A - 600 V - very fast IGBT

## Features

- Low on-voltage drop ( $V_{CE(sat)}$ )
- Low  $C_{RES} / C_{IES}$  ratio (no cross-conduction susceptibility)
- Very soft ultra fast recovery anti-parallel diode

## Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies
- Motor drives

## Description

This IGBT utilizes the advanced Power MESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

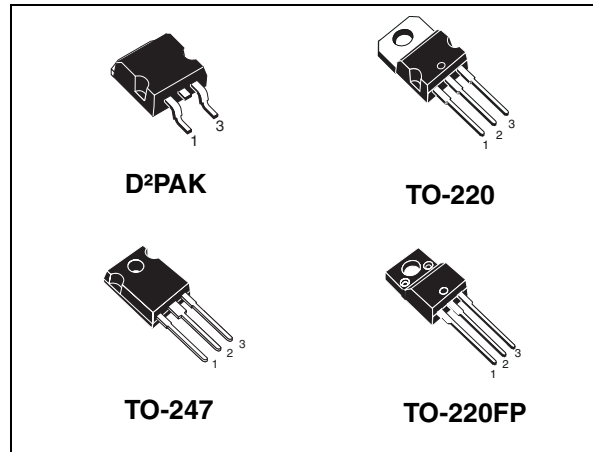


Figure 1. Internal schematic diagram

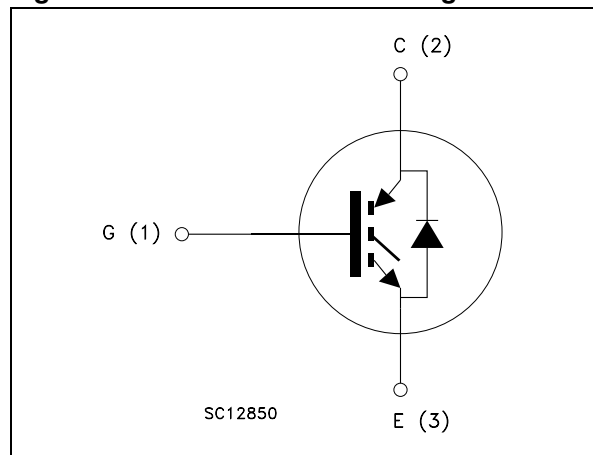


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB19NC60HDT4	GB19NC60HD	D <sup>2</sup> PAK	Tape and reel
STGF19NC60HD	GF19NC60HD	TO-220FP	Tube
STGP19NC60HD	GP19NC60HD	TO-220	Tube
STGW19NC60HD	GW19NC60HD	TO-247	Tube

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value			Unit
		TO-220 D <sup>2</sup> PAK	TO-220FP	TO-247	
V <sub>CES</sub>	Collector-emitter voltage (V <sub>GE</sub> = 0)	600			V
I <sub>C</sub> <sup>(1)</sup>	Collector current (continuous) at T <sub>C</sub> = 25 °C	40	16	42	A
I <sub>C</sub> <sup>(1)</sup>	Collector current (continuous) at T <sub>C</sub> = 100 °C	19	10	21	A
I <sub>CL</sub> <sup>(2)</sup>	Turn-off latching current	40			A
I <sub>CP</sub> <sup>(3)</sup>	Pulsed collector current	40			A
I <sub>F</sub>	Diode RMS forward current at T <sub>C</sub> = 25 °C	20			A
I <sub>FSM</sub>	Surge not repetitive forward current t <sub>p</sub> =10 ms sinusoidal	50			A
V <sub>GE</sub>	Gate-emitter voltage	±20			V
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	130	32	140	W
V <sub>ISO</sub>	Isolation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T <sub>C</sub> = 25 °C)	2500			V
T <sub>j</sub>	Operating junction temperature	– 55 to 150			°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C) \cdot I_C}$$

2. V<sub>clamp</sub>=80%V<sub>CES</sub>, T<sub>J</sub>= 150 °C, R<sub>G</sub>=1 0 Ω, V<sub>GE</sub> = 15 V

3. Pulse width limited by max. temperature allowed

**Table 3. Thermal resistance**

Symbol	Parameter	Value			Unit
		TO-220 D <sup>2</sup> PAK	TO-220FP	TO-247	
R <sub>thj-case</sub>	Thermal resistance junction-case IGBT max.	0.95	3.9	0.9	°C/W
	Thermal resistance junction-case diode max.	3	5.5	3	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction- ambient max.	62.5		50	°C/W

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}\text{C}$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ( $V_{GE}=0$ )	$I_C=1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE}=15\text{ V}, I_C=12\text{ A}$ $V_{GE}=15\text{ V}, I_C=12\text{ A}, T_C=125^{\circ}\text{C}$		1.8 1.6	2.5	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE}=V_{GE}, I_C=250\text{ }\mu\text{A}$	3.75		5.75	V
$I_{CES}$	Collector cut-off current ( $V_{GE}=0$ )	$V_{CE}=600\text{ V}$ $V_{CE}=600\text{ V}, T_C=125^{\circ}\text{C}$			150 1	$\mu\text{A}$ mA
$I_{GES}$	Gate-emitter leakage current ( $V_{CE}=0$ )	$V_{GE}=\pm 20\text{ V}$			$\pm 100$	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE}=15\text{ V}, I_C=12\text{ A}$		5		S

1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance			1180		pF
$C_{oes}$	Output capacitance	$V_{CE}=25\text{ V}, f=1\text{ MHz},$		130		pF
$C_{res}$	Reverse transfer capacitance	$V_{GE}=0$		36		pF
$Q_g$	Total gate charge	$V_{CE}=390\text{ V}, I_C=5\text{ A},$		53		nC
$Q_{ge}$	Gate-emitter charge	$V_{GE}=15\text{ V},$		10		nC
$Q_{gc}$	Gate-collector charge	<a href="#">Figure 20</a>		23		nC

**Table 6. Switching on/off (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$ $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , <i>Figure 21</i>		25 7 1600		ns ns A/ $\mu$ s
$t_{d(on)}$ $t_r$ $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , $T_C = 125\text{ }^\circ\text{C}$ <i>Figure 21</i>		24 8 1400		ns ns A/ $\mu$ s
$t_{r(Voff)}$ $t_{d(Voff)}$ $t_f$	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , <i>Figure 21</i>		27 97 73		ns ns ns
$t_{r(Voff)}$ $t_{d(Voff)}$ $t_f$	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , $T_C = 125\text{ }^\circ\text{C}$ <i>Figure 21</i>		58 144 128		ns ns ns

**Table 7. Switching energy (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}$ $E_{off}^{(1)}$ $E_{ts}$	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , <i>Figure 21</i>		85 189 274		$\mu$ J $\mu$ J $\mu$ J
$E_{on}$ $E_{off}^{(1)}$ $E_{ts}$	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$ $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , $T_C = 125\text{ }^\circ\text{C}$ <i>Figure 21</i>		187 407 594		$\mu$ J $\mu$ J $\mu$ J

1. Turn-off losses include also the tail of the collector current

Table 8. Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward on-voltage	$I_F = 12\text{ A}$		2.6		V
		$I_F = 12\text{ A}, T_C = 125\text{ °C}$		2.1		V
$t_{rr}$	Reverse recovery time	$I_F = 12\text{ A}, V_R = 40\text{ V},$ $di/dt = 100\text{ A}/\mu\text{s}$		31		ns
$Q_{rr}$	Reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$		30		nC
$I_{rrm}$	Reverse recovery current	<a href="#">Figure 22</a>		2		A
$t_{rr}$	Reverse recovery time	$I_F = 12\text{ A}, V_R = 40\text{ V},$ $T_C = 125\text{ °C}, di/dt = 100\text{ A}/\mu\text{s}$		59		ns
$Q_{rr}$	Reverse recovery charge	$T_C = 125\text{ °C}, di/dt = 100\text{ A}/\mu\text{s}$		102		nC
$I_{rrm}$	Reverse recovery current	<a href="#">Figure 22</a>		4		A

## 2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

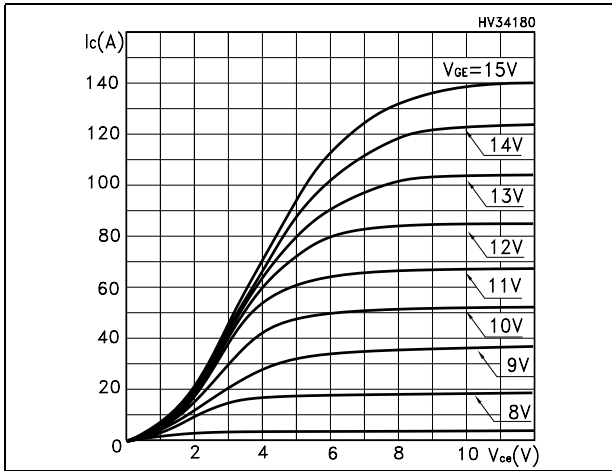


Figure 3. Transfer characteristics

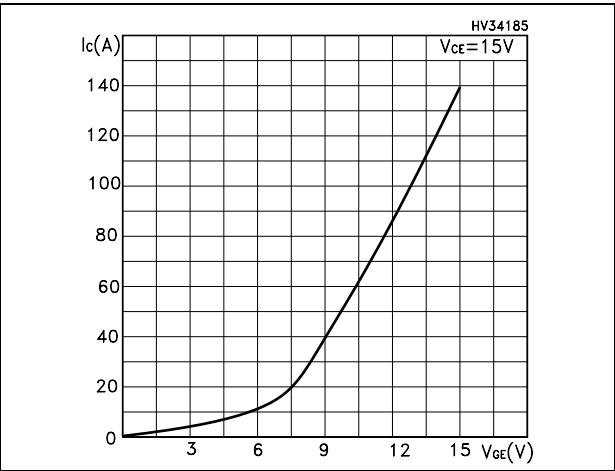


Figure 4. Transconductance

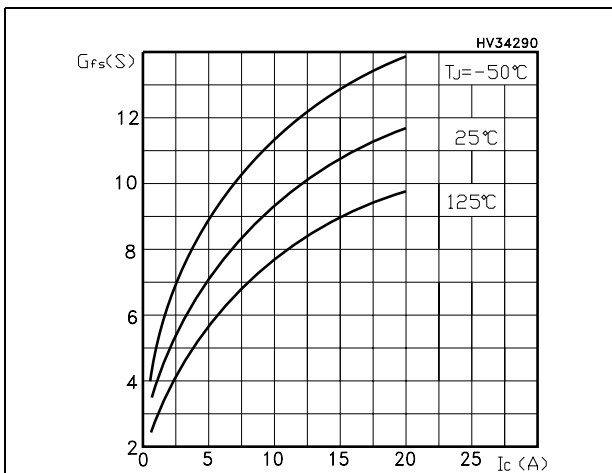


Figure 5. Collector-emitter on voltage vs temperature

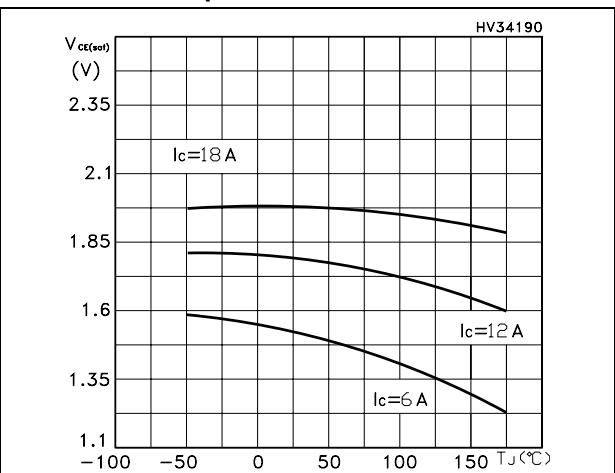


Figure 6. Gate charge vs gate-source voltage

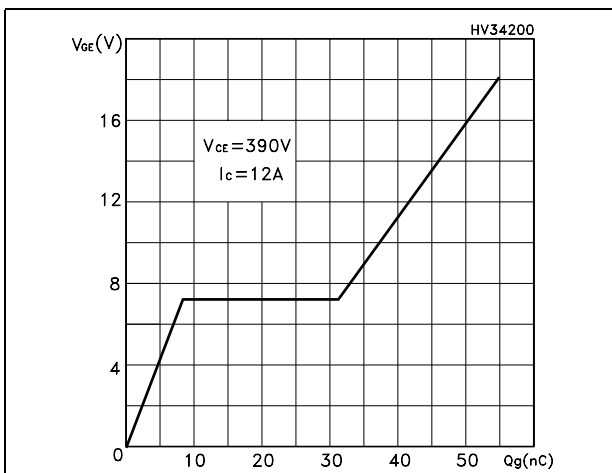
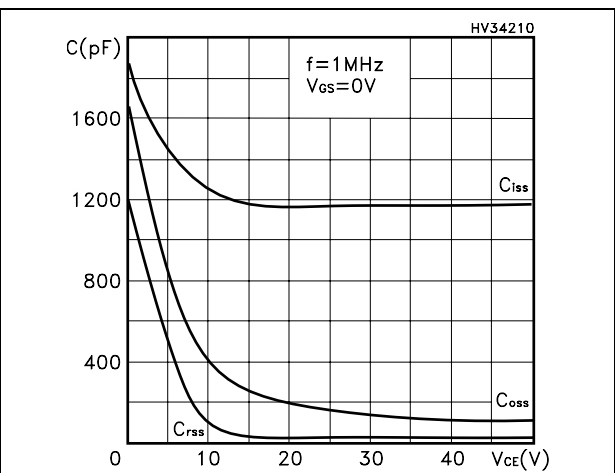
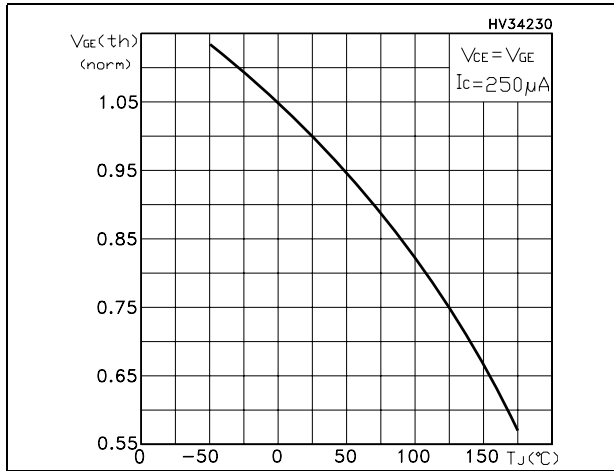


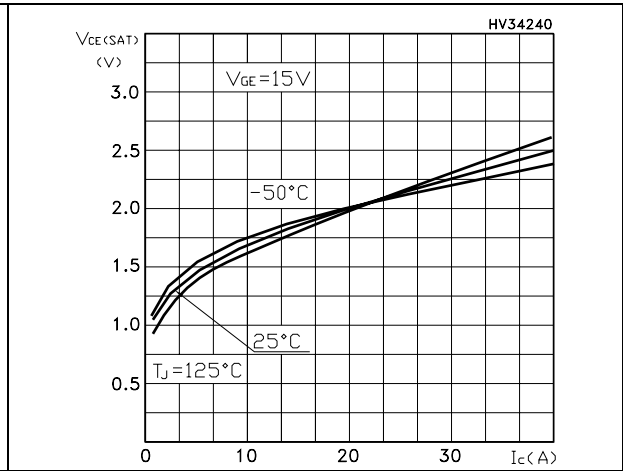
Figure 7. Capacitance variations



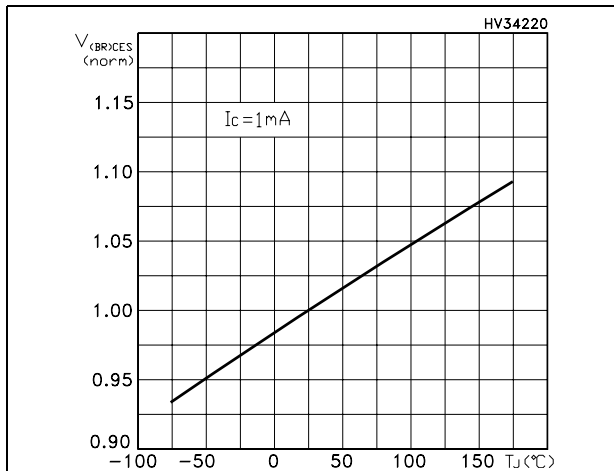
**Figure 8. Normalized gate threshold voltage vs temperature**



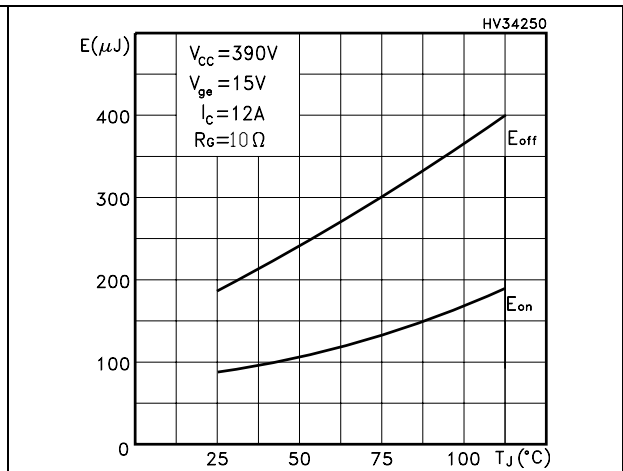
**Figure 9. Collector-emitter on voltage vs collector current**



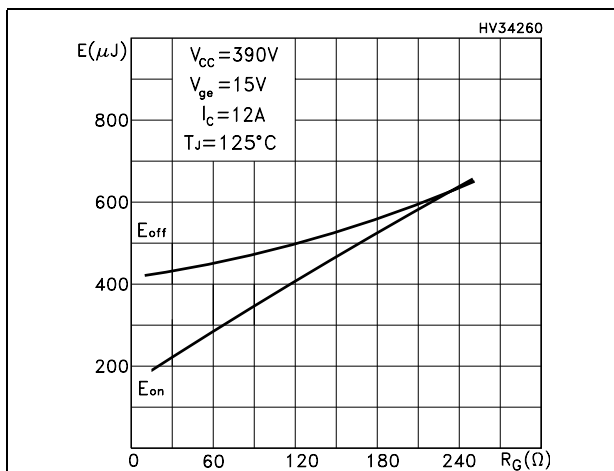
**Figure 10. Normalized breakdown voltage vs temperature**



**Figure 11. Switching losses vs temperature**



**Figure 12. Switching losses vs gate resistance**



**Figure 13. Switching losses vs collector current**

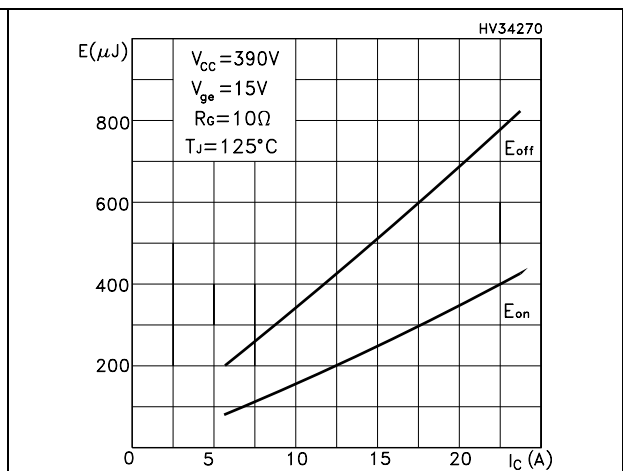




Figure 14. Turn-off SOA

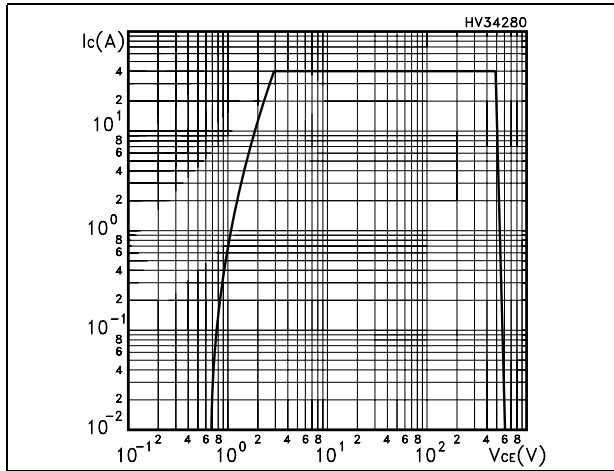


Figure 15. Forward voltage drop versus forward current

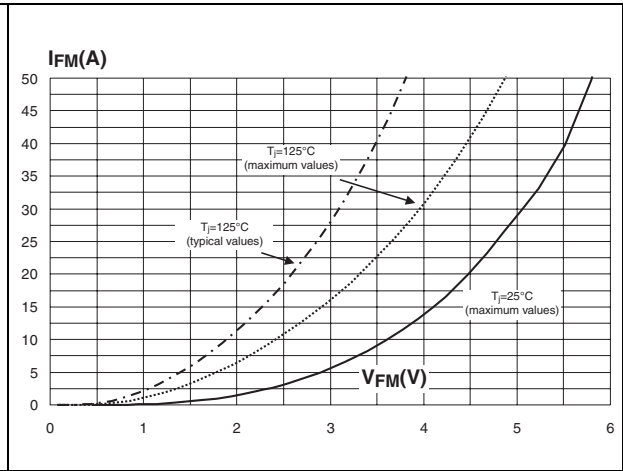


Figure 16. Thermal impedance for TO-220 D<sup>2</sup>PAK

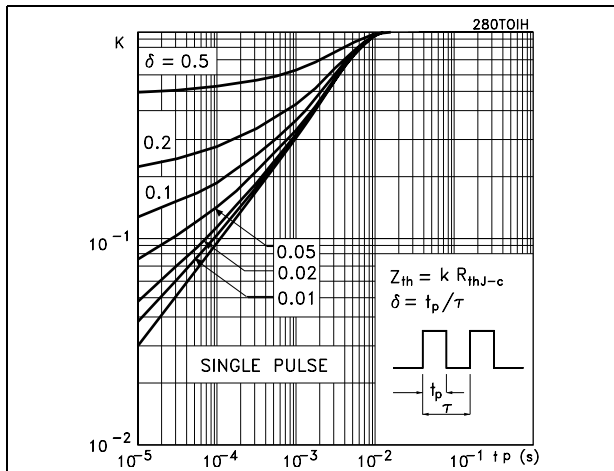


Figure 17. Thermal impedance for TO-220FP

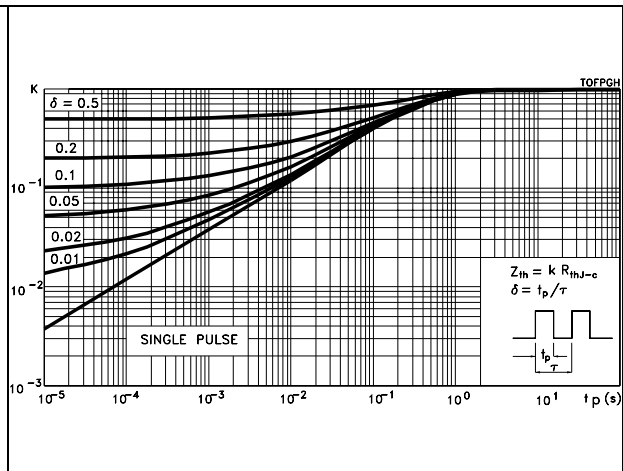
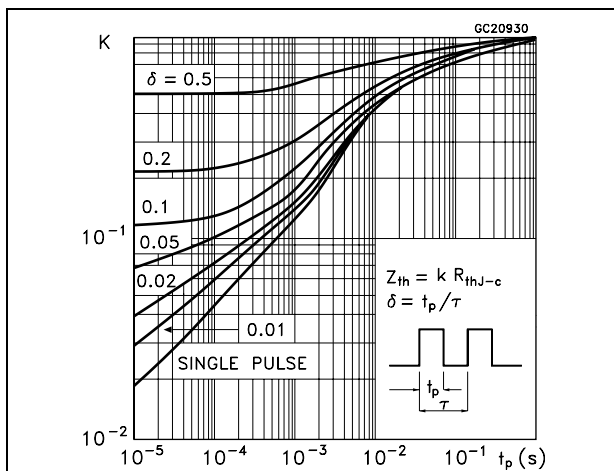


Figure 18. Thermal impedance for TO-247



### 3 Test circuits

Figure 19. Test circuit for inductive load switching

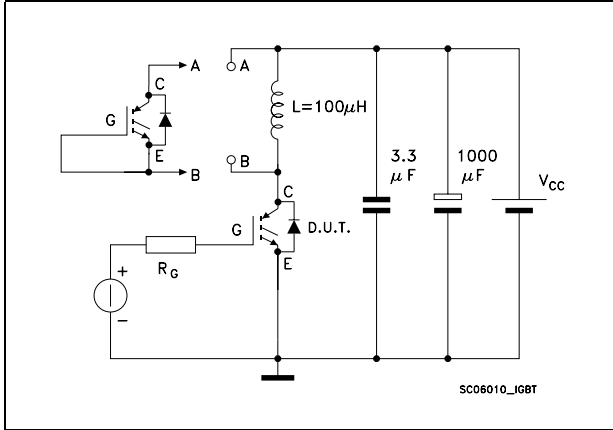


Figure 21. Switching waveform

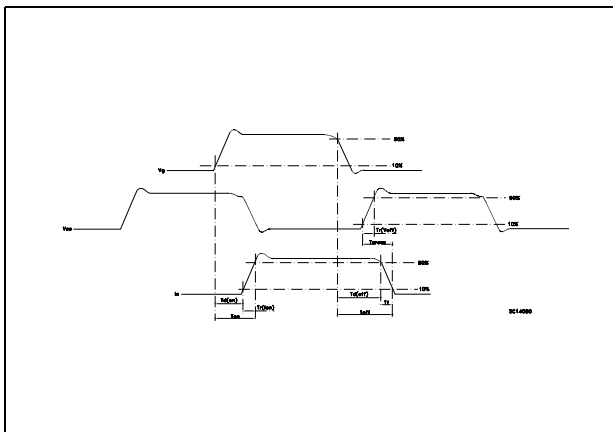


Figure 20. Gate charge test circuit

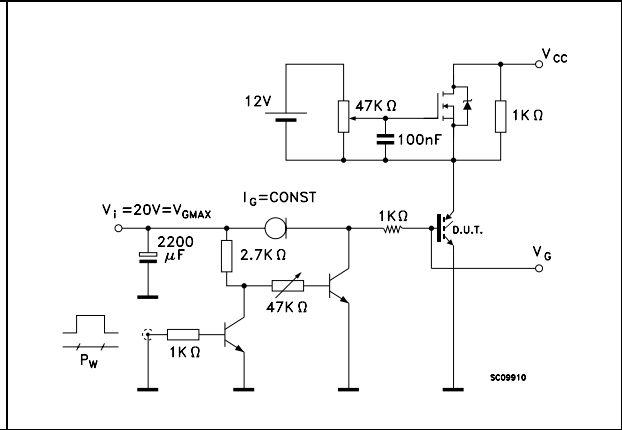
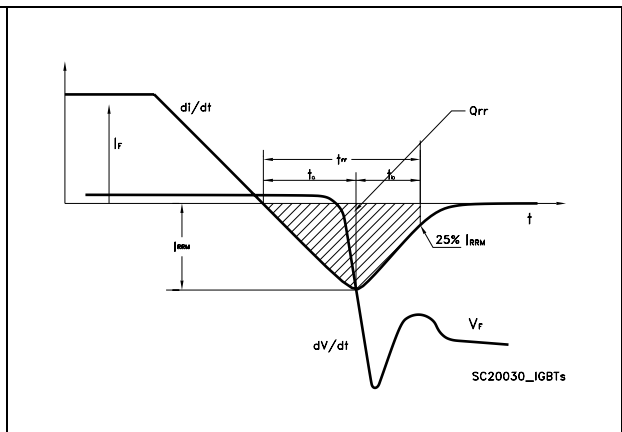


Figure 22. Diode recovery time waveform

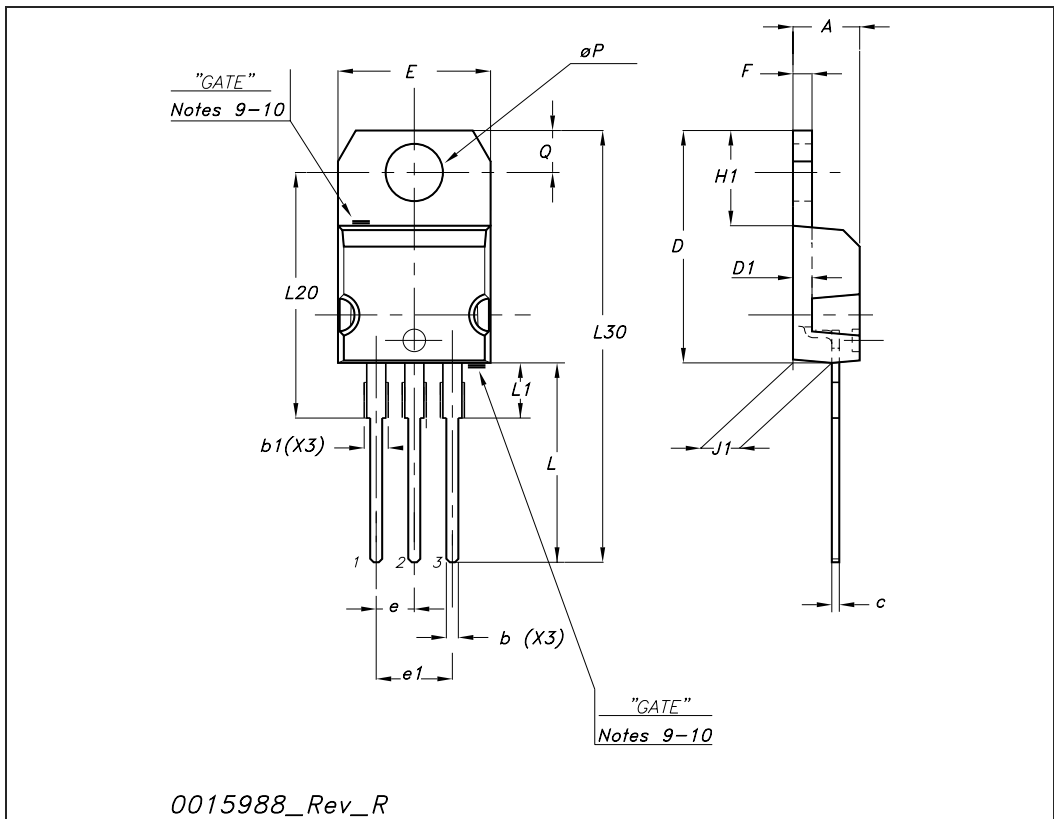


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

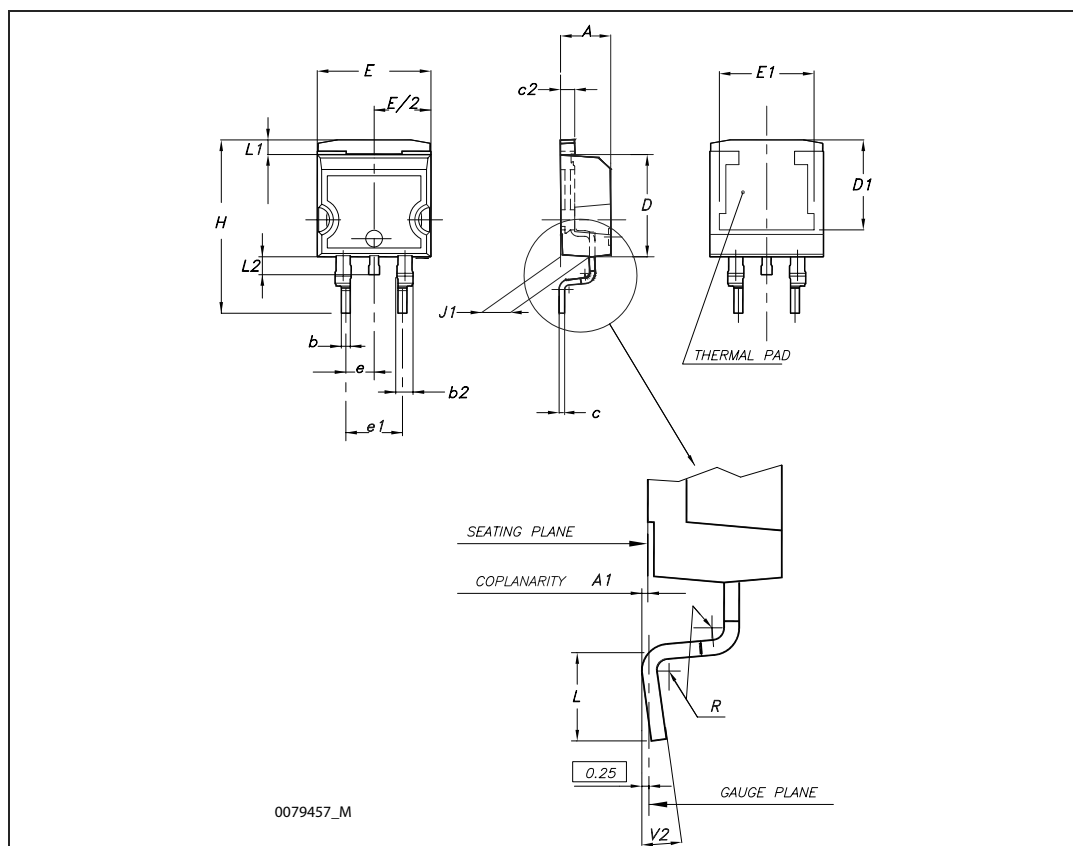
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



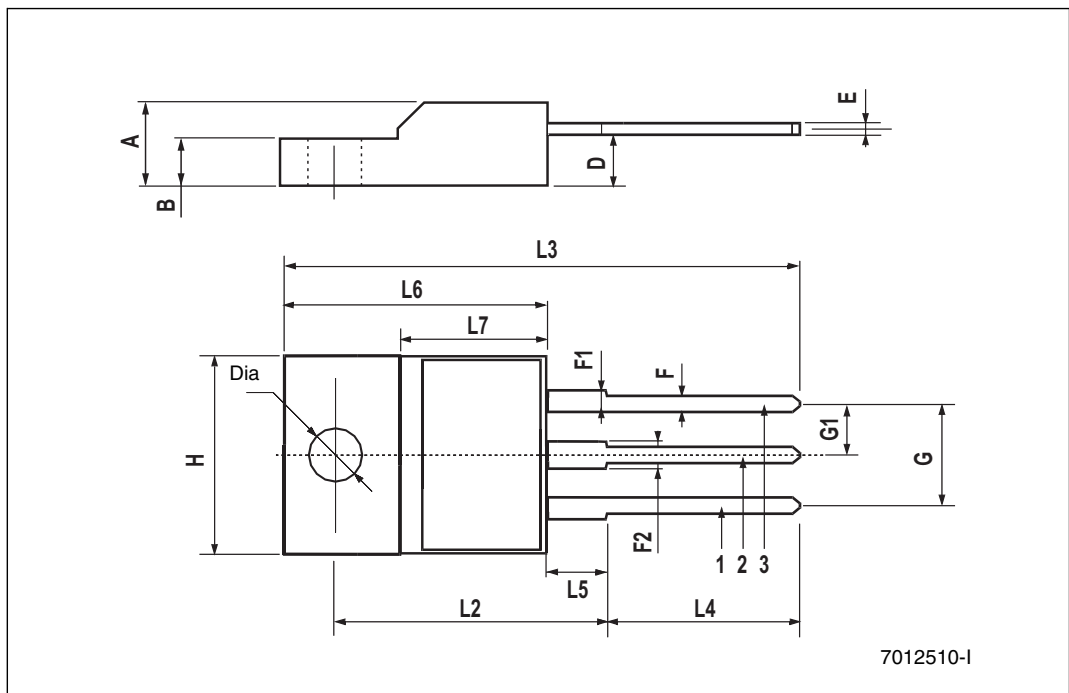
D<sup>2</sup>PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



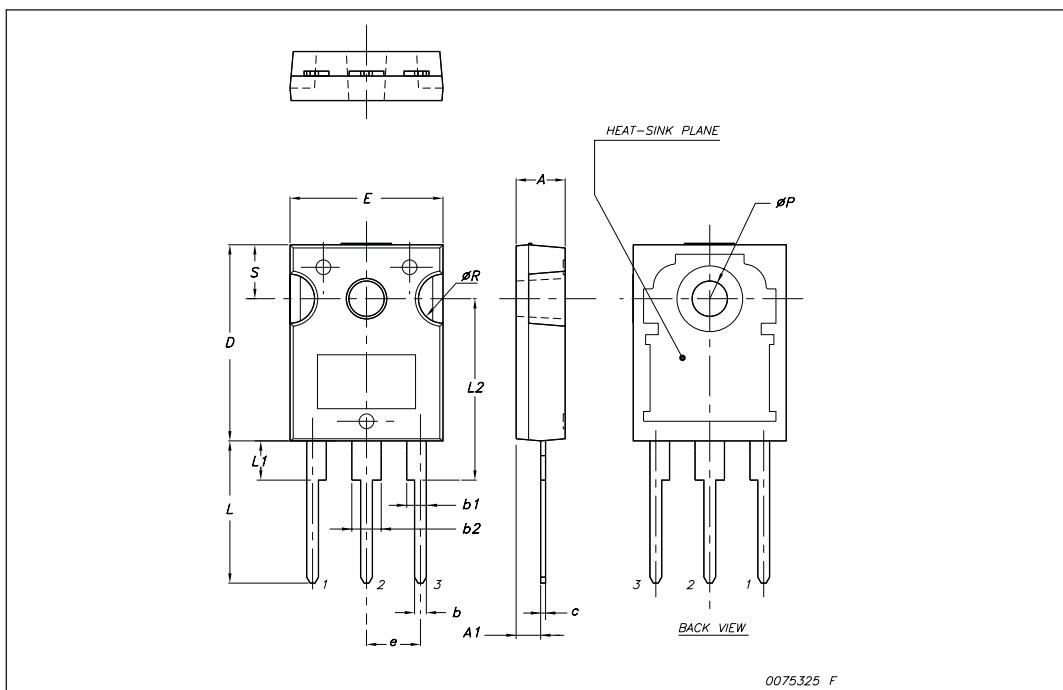
**TO-220FP mechanical data**

Dim.	mm.			inch		
	Min.	Typ	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.70	0.017		0.027
F	0.75		1.00	0.030		0.039
F1	1.15		1.50	0.045		0.067
F2	1.15		1.50	0.045		0.067
G	4.95		5.20	0.195		0.204
G1	2.40		2.70	0.094		0.106
H	10		10.40	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.80		10.60	0.385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.90		16.40	0.626		0.645
L7	9		9.30	0.354		0.366
Dia	3		3.2	0.118		0.126



**TO-247 mechanical data**

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



# 5 Packaging mechanical data

## D<sup>2</sup>PAK FOOTPRINT



## TAPE AND REEL SHIPMENT

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

\* on sales type



## 6 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
02-Nov-2006	1	Initial release.
05-Jan-2007	2	Complete version
01-Jul-2008	3	– Modified: <a href="#">Table 2: Absolute maximum ratings</a> – Inserted new packages, mechanical data: TO-220FP, TO-247
13-Oct-2008	4	V <sub>ISO</sub> inserted in <a href="#">Table 2</a> for TO-220FP

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